

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-70. (Canceled)

71. (Previously presented) A semiconductor device having at least a static random access memory, the static random access memory comprising:

a word line over a substrate;

a bit line intersecting perpendicularly to the word line, over the substrate; and

at least a first thin film transistor and a second thin film transistor over the substrate;

wherein a gate electrode of the first thin film transistor is connected to a source or drain region of the second thin film transistor,

wherein a gate electrode of the second thin film transistor is connected to a source or drain region of the first thin film transistor, and electrically connected to the bit line,

each of the first and second thin film transistors comprising:

a crystalline semiconductor film comprising silicon on an insulating film,

wherein the insulating film has at least one asperity of less than 30Å in height on the upper surface thereof.

72. (Previously presented) A semiconductor device having at least a static random access memory according to claim 71, wherein the static random access memory further comprising:

a first resistor connected to a source or drain region of the first thin film transistor;

a second resistor connected to a source or drain region of the second thin film transistor.

73. (Previously presented) A semiconductor device having at least a static random access memory according to claim 71, wherein the static random access memory further comprising:

a third thin film transistor provided between a source or drain region of the first thin film transistor and the bit line; and

a fourth thin film transistor provided between a source or drain region of the second thin film transistor and the word line,

wherein gate electrodes of the third and fourth thin film transistor are connected to the word line.

74. (Previously presented) A semiconductor device having at least a static random access memory according to claim 71, wherein the insulating film comprises silicon oxide.

75. (Previously presented) A semiconductor device having at least a static random access memory according to claim 71, wherein the asperity has a width more than 100 Å.

76. (Previously presented) A static random access memory according to claim 71, wherein crystals of the crystalline semiconductor film extend in parallel with the substrate.

77. (Previously presented) An electronic appliance comprising the semiconductor device having at least a static random access memory according to claim 71, wherein the electronic appliance is selected from the group consisting of a TV camera, a head-mount display, a car navigation, a projection display, a video camera, a personal computer, and a cellular telephone.

78. (New) A computer comprising:

an operation switch; and

a display device, the display device comprising:

a substrate;

an insulating film over the substrate; and

a crystalline semiconductor film comprising silicon formed on the insulating film, wherein the insulating film has at least one asperity of less than 30 Å in height on the upper surface thereof.

79. (New) A computer according to claim 78, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

80. (New) A computer according to claim 78, wherein the insulating film comprises silicon oxide.

81. (New) A computer comprising:
an operation switch; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of less than 30 Å in height on the upper surface thereof; and
a crystalline semiconductor film comprising silicon formed on the insulating film, wherein the asperity has a width more than 100 Å.

82. (New) A computer according to claim 81, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

83. (New) A computer according to claim 81, wherein the insulating film comprises silicon oxide.

84. (New) A computer according to claim 81, wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

85. (New) A computer comprising:
an operation switch; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of less than 30 Å in height on the upper surface thereof;
a crystalline semiconductor film comprising silicon formed on the insulating film, wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

86. (New) A computer according to claim 85, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

87. (New) A computer according to claim 85, wherein the insulating film comprises silicon oxide.

88. (New) A computer according to claim 85, wherein the asperity has a width more than 100 Å.

89. (New) A cellular phone comprising:
a voice output section;
a voice input section; and
a display device, the display device comprising:
a substrate;

an insulating film over the substrate; and
a crystalline semiconductor film comprising silicon formed on the insulating film,
wherein the insulating film has at least one asperity of less than 30 Å in height on the
upper surface thereof.

90. (New) A cellular phone according to claim 89, wherein the camera further
comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the
gate insulating film.

91. (New) A cellular phone according to 89, wherein the insulating film comprises
silicon oxide.

92. (New) A cellular phone comprising:
a voice output section;
a voice input section; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of
less than 30 Å in height on the upper surface thereof; and
a crystalline semiconductor film comprising silicon formed on the insulating film,
wherein the asperity has a width more than 100 Å.

93. (New) A cellular phone according to claim 92, wherein the camera further
comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the
gate insulating film.

94. (New) A cellular phone according to claim 92, wherein the insulating film
comprises silicon oxide.

95. (New) A cellular phone according to claim 92, wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

96. (New) A cellular phone comprising:
a voice output section;
a voice input section; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of less than 30 Å in height on the upper surface thereof;
a crystalline semiconductor film comprising silicon formed on the insulating film, wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

97. (New) A cellular phone according to claim 96, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

98. (New) A cellular phone according to claim 96, wherein the insulating film comprises silicon oxide.

99. (New) A cellular phone according to claim 96, wherein the asperity has a width more than 100 Å.

100. (New) A camera comprising:
an operation switch;
an image receiving section; and

a display device, the display device comprising:
a substrate;
an insulating film over the substrate; and
a crystalline semiconductor film comprising silicon formed on the insulating film,
wherein the insulating film has at least one asperity of less than 30 Å in height on the
upper surface thereof.

101. (New) A camera according to claim 100, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

102. (New) A camera according to 100, wherein the insulating film comprises silicon oxide.

103. (New) A camera comprising:
an operation switch;
an image receiving section; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of less than 30 Å in height on the upper surface thereof; and
a crystalline semiconductor film comprising silicon formed on the insulating film,
wherein the asperity has a width more than 100 Å.

104. (New) A camera according to claim 103, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

105. (New) A camera according to claim 103, wherein the insulating film comprises silicon oxide.

106. (New) A camera according to claim 103, wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

107. (New) A camera comprising:
an operation switch;
an image receiving section; and
a display device, the display device comprising:
a substrate;
an insulating film over the substrate, the insulating film having at least one asperity of less than 30 Å in height on the upper surface thereof;
a crystalline semiconductor film comprising silicon formed on the insulating film,
wherein crystals of the crystalline semiconductor film extend in parallel with the insulating film.

108. (New) A camera according to claim 107, wherein the camera further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

109. (New) A camera according to claim 107, wherein the insulating film comprises silicon oxide.

110. (New) A camera according to claim 107, wherein the asperity has a width more than 100 Å.